

AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended): A resist composition comprising a fluoropolymer (A);  
an acid-generating compound (B) which generates an acid under irradiation with light; and an  
organic solvent (C), wherein

the fluoropolymer (A) which is a fluoropolymer having repeating units formed by  
cyclopolymerization of a fluorinated diene represented by the formula (1)



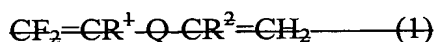
where

each of R<sup>1</sup> and R<sup>2</sup>, which are independent of each other, is a hydrogen atom, a  
fluorine atom, a methyl group or a trifluoromethyl group;

Q is a bivalent organic group having a blocked acidic group capable of  
forming an acidic group by an acid or a group which can be converted to such a blocked  
acidic group;

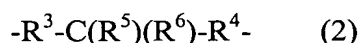
the fluorinated diene and which has blocked acidic groups, ~~provided that ; and~~  
in a case where Q is a the bivalent organic group having a group which can be  
converted to a blocked acidic group, said group is converted to a blocked acidic group after  
the cyclopolymerization

~~, an acid-generating compound (B) which generates an acid under irradiation with~~  
~~light, and an organic solvent (C);~~



~~wherein each of R<sup>1</sup> and R<sup>2</sup> which are independent of each other, is a hydrogen atom, a~~  
~~fluorine atom, a methyl group or a trifluoromethyl group, and Q is a bivalent organic group~~  
~~having a blocked acidic group capable of forming an acidic group by an acid or a group~~  
~~which can be converted to such a blocked acidic group.~~

Claim 2 (Currently Amended): The resist composition according to Claim 1, wherein Q is a bivalent organic group represented by the formula (2):



~~wherein~~ where

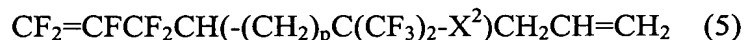
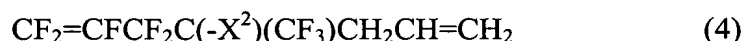
each of  $R^3$  and  $R^4$ , which are independent of each other, is a single bond, an oxygen atom, an alkylene group having at most 3 carbon atoms, which may have an etheric oxygen atom, or a fluoroalkylene group having at most 3 carbon atoms, which may have an etheric oxygen ~~atom,~~ atom;

$R^5$  is a hydrogen atom, a fluorine atom, an alkyl group having at most 3 carbon atoms or a fluoroalkyl group having at most 3 carbon ~~atoms,~~ atoms; and

$R^6$  is a blocked acidic group, an acidic group, or a monovalent organic group having a blocked acidic group or an acidic group.

Claim 3 (Original): The resist composition according to Claim 1, wherein the acidic group is an acidic hydroxyl group, and the blocked acidic group is a blocked acidic hydroxyl group.

Claim 4 (Currently Amended): The resist composition according to Claim 1, wherein the fluorinated diene is a fluorinated diene represented by the formula (4) or (5):



~~wherein~~ where

$\text{X}^2$  is  $\text{O}(\text{t-C}_4\text{H}_9)$ ,  $\text{OCH}_2\text{OCH}_3$ ,  $\text{OCOO}(\text{t-C}_4\text{H}_9)$ ,  $\text{OCH}(\text{CH}_3)\text{OC}_2\text{H}_5$  or a

2-tetrahydropyranyloxy group, ~~and~~ ; and

$p$  is an integer of from 1 to 3.

Claim 5 (Currently Amended) The resist composition according to Claim 1, wherein the fluoropolymer (A) is a copolymer comprising

repeating units formed by cyclopolymerization of a the fluorinated diene represented by the formula (1) and

repeating units formed by polymerization of other monomers, ~~wherein~~ ; and  
the proportion of the repeating units formed by polymerization of other monomers is at most 30 mol%.

Claim 6 (Currently Amended): ~~The A method of using a resist composition, the method comprising exposing the~~ resist composition according to Claim 1, ~~which is a resist composition for exposure by~~ to ultraviolet rays having a wavelength of at most 200 nm.

Claim 7 (Currently Amended): The ~~resist composition~~ method according to Claim 6, wherein the ultraviolet rays having a wavelength of at most 200 nm are in ArF excimer laser beams or  $\text{F}_2$  excimer laser beams.

Claim 8 (Currently Amended): A process for forming a pattern, ~~which comprises the~~  
process comprising

coating the resist composition ~~as defined in~~ of Claim 1 on a substrate,  
then removing the organic solvent (C) to form a thin film of a resist comprising the  
fluoropolymer (A) and the acid-generating compound (B), ~~and~~  
then irradiating the thin film with ultraviolet rays having a wavelength of at most 200  
nm ~~capable of~~ ,  
generating an acid from the acid-generating compound (B) ~~to form a~~ , and  
forming the pattern.

Claim 9 (Currently Amended): The process according to Claim 8, wherein the  
ultraviolet rays having a wavelength of at most 200 nm are in ArF excimer laser beams or F<sub>2</sub>  
excimer laser beams.